

Supporting Information

High-performance Inverted Organic Light-emitting Diodes with Extremely Low Efficiency Roll-off using Solution-processed ZnS Quantum Dots as Electron Injection Layer

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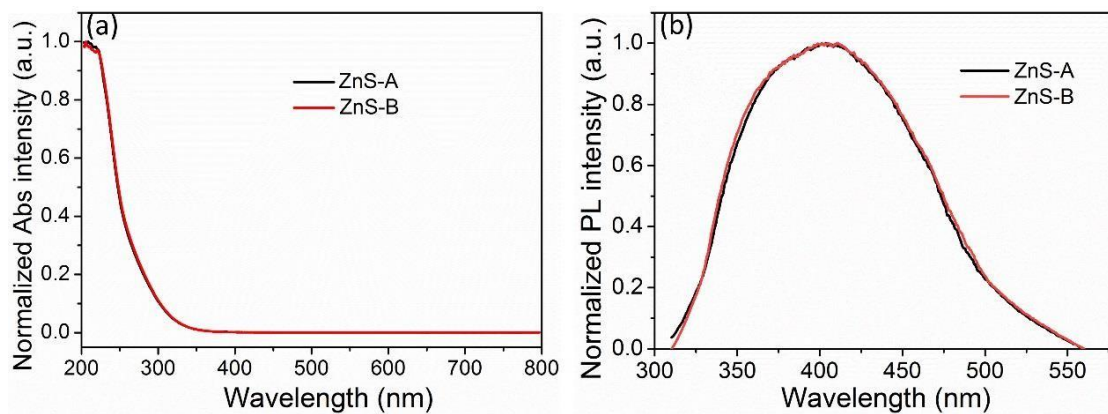


Figure S1. Absorption and Photoluminescence spectra of ZnS-A and ZnS-B film spin-coated on glass substrate.

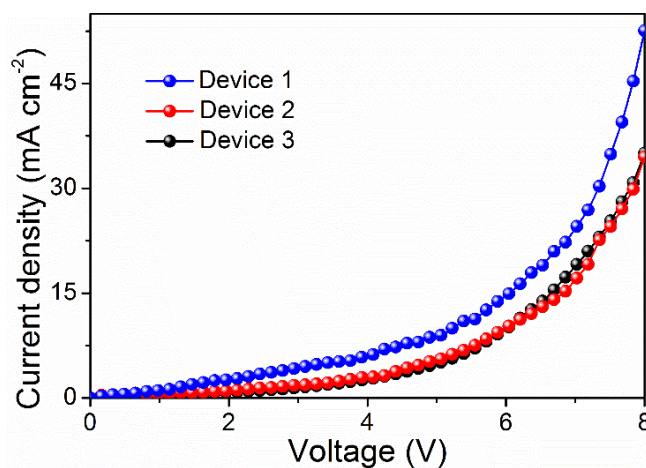


Figure S2. The current density-voltage characteristics of electron-only devices (EODs) 1, 2 and 3.

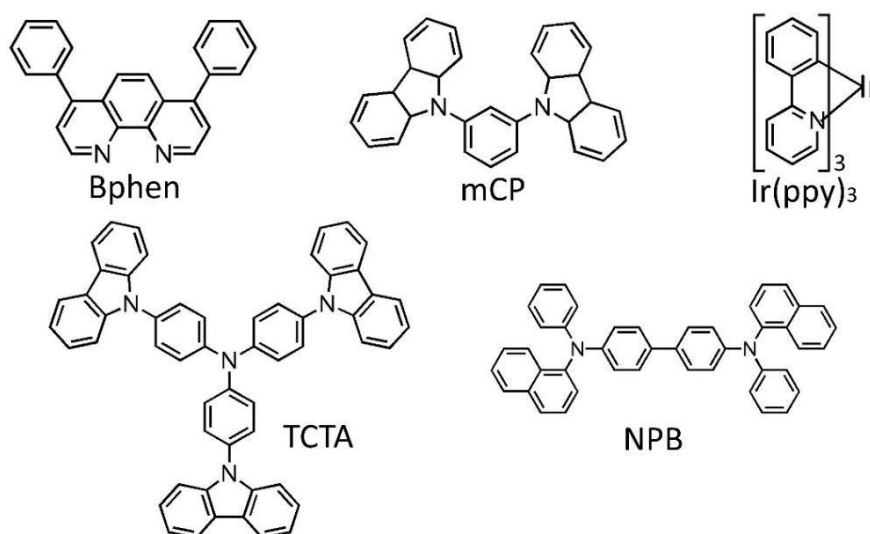


Figure S3. Chemical structures of the materials described in the inverted OLED devices

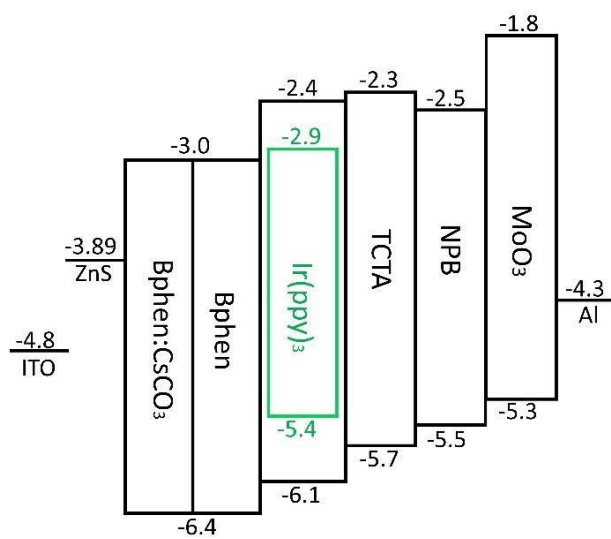


Figure S4. The corresponding energy level diagram of inverted OLED devices.